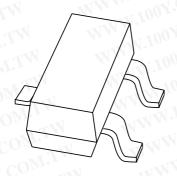
DISCRETE SEMICONDUCTORS

DATA SHEET



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MMBT3904 NPN switching transistor

Product specification Supersedes data of 2002 Oct 04

2004 Feb 03





Philips Semiconductors Product specification

NPN switching transistor

MMBT3904

FEATURES

- Collector current capability I_C = 200 mA
- Collector-emitter voltage V_{CEO} = 40 V.

APPLICATIONS

General switching and amplification.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package. PNP complement: MMBT3906.

MARKING

TYPE NUMBER	MARKING CODE(1)
MMBT3904	7A*

Note

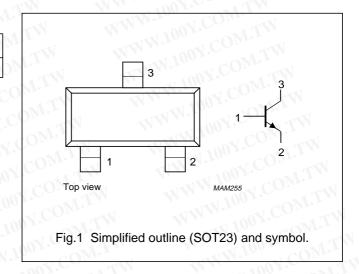
- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	40	V
I _C	collector current (DC)	200	mA

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

	TOO COM	PACKAGE	N. 100 Y.CO	
TYPE NUMBER	NAME	DESCRIPTION	VERSION	
MMBT3904	M.100-V.CC	plastic surface mounted package; 3 leads	SOT23	
		COMITY WWW.100Y.COMITY		

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2004 Feb 03 2

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
V _{CBO}	collector-base voltage	open emitter	COMP	60	V	
V _{CEO}	collector-emitter voltage	open base	COM	40	V	
V _{EBO}	emitter-base voltage	open collector	TOM.	6	V	
lc 1	collector current (DC)	1.77	ON-TOM!	200	mA	
I _{CM}	peak collector current	TW WWW	001	200	mA	
I _{BM} (O)	peak base current	IN MAN.	100 Y.CO	100	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-TV.CO	250	mW	
T _{stg}	storage temperature	ON	-65	+150	°C	
T _{j1} 00 y	junction temperature	COMITY	M 700 1.	150	°C	
T _{amb}	operating ambient temperature	N. W.	-65	+150	°C	

Note Note

THERMAL CHARACTERISTICS

Note 1. Transisto	r mounted o	n an FR4 printed-circuit board.			
THERMAL C	HARACTER	RISTICS	OM.TV V	MM.100X.C	M.TW
SYMBOL	ON.COM	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thormalro	sistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

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CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	\overline{O}_{Mr}	50	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 6 V	$\mathfrak{O}_{M_{I}}$	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; see Fig.2; note 1	COM.	-	
	IN MM. 100X.C.	$I_{C} = 0.1 \text{ mA}$	60	17	
	LM MM 100X.	I _C = 1 mA	80	TW	
	WWW.IOW	I _C = 10 mA	100	300	
	W. TOWN. 100	I _C = 50 mA	60	- TW	
	W.1., W. W. 100	I _C = 100 mA	30	M	
V _{CEsat}	collector-emitter saturation	I _C = 10 mA; I _B = 1 mA	700 2	200	mV
	voltage	I _C = 50 mA; I _B = 5 mA	1-100 x	300	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	650	850	mV
	COM.	I _C = 50 mA; I _B = 5 mA	700	950	mV
C _c	collector capacitance	I _E = I _e = 0; V _{CB} = 5 V; f = 1 MHz	TN. Jo	4	pF
C _e	emitter capacitance	$I_C = I_c = 0$; $V_{BE} = 500 \text{ mV}$; $f = 1 \text{ MHz}$	W.IO	8	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 20 V; f = 100 MHz	300	10 0 1.CC	MHz
FWWW	noise figure	I_C = 100 μA; V_{CE} = 5 V; R_S = 1 kΩ; f = 10 Hz to 15.7 kHz	-WWW	5 100Y.C	dB
Switching t	imes (between 10% and 90% lev	els); see Fig.3	MM	1001	-oM.
t _d	delay time	I _{Con} = 10 mA; I _{Bon} = 1 mA;	- 111	35	ns
t _r	rise time	I _{Boff} = -1 mA	- 1	35	ns
t _s	storage time	MW.100 COM.	-	200	ns
t _f	fall time	W. 1001. COW.I.	_	50	ns

Note

1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$ WWW.100Y.COM.TW

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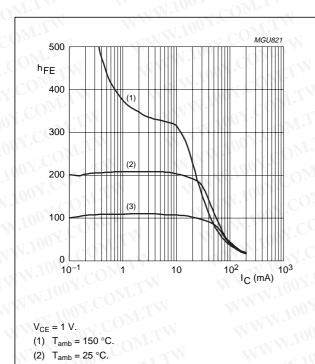
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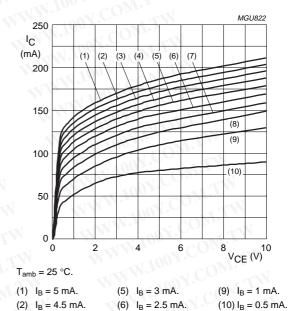
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NPN switching transistor

MMBT3904





- (7) $I_B = 2 \text{ mA}$.

- (3) $I_B = 4 \text{ mA}$.
- (4) $I_B = 3.5 \text{ mA}.$ (8) $I_B = 1.5 \text{ mA}.$

Fig.3 Collector current as a function of collector-emitter voltage.

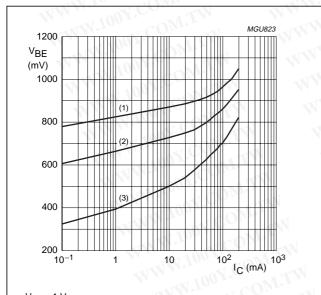
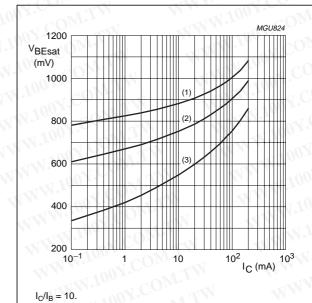


Fig.2 DC current gain; typical values.



 $V_{CE} = 1 V$.

(1) $T_{amb} = -55 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.4 Base-emitter voltage as a function of collector current.

(2) $T_{amb} = 25 \, ^{\circ}C$. (3) $T_{amb} = 150 \, ^{\circ}C$.

(1) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current.

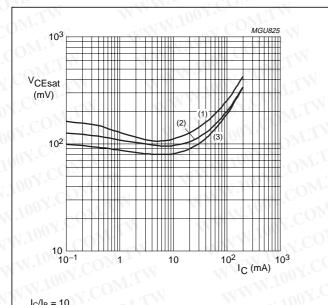
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 $I_{\rm C}/I_{\rm B} = 10$.

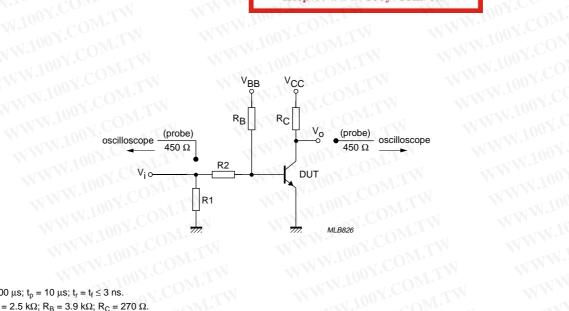
- (1) $T_{amb} = 150 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

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Fig.6 Collector-emitter saturation voltage as a function of collector current.

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 $V_i = 5 \text{ V}; T = 500 \text{ } \mu\text{s}; t_p = 10 \text{ } \mu\text{s}; t_r = t_f \leq 3 \text{ ns}.$ $\label{eq:continuous} \text{J}_{c} = -1.8 \text{ v; } V_{CC} = 3 \text{ V.}$ Oscilloscope: input impedance $Z_i = 50 \ \Omega.$

Fig.7 Test circuit for switching times.

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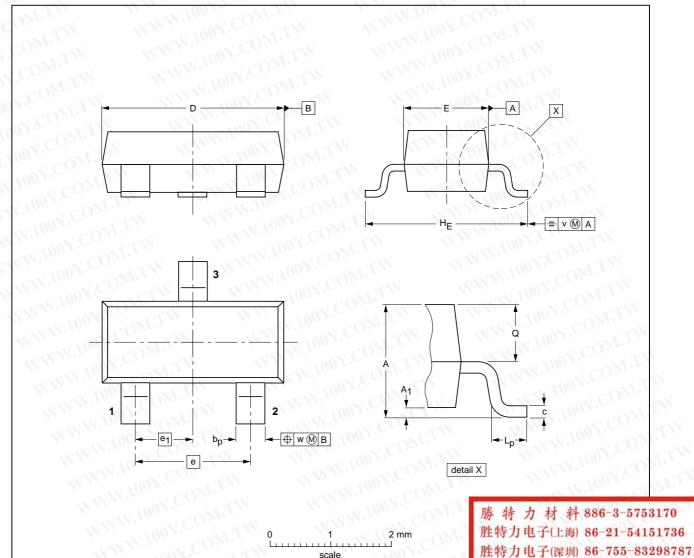
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁ max.	bp	l · c	DC	OF.	e	e ₁	HE	Lp	Q	V.CC	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE	M. M.	REFER	W 100	EUROPEAN	IOOUE DATE	
VERSION	IEC	JEDEC	EIAJ	WWW	PROJECTION	ISSUE DATE
SOT23	WW	TO-236AB	WILL	MMM		97-02-28 99-09-13

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
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100X·CO	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
M.100 M.100 A	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

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